

30V 22A Dual N-Channel Enhancement Mode Power MOSFET

General Description

This Power MOSFET has been developed using advanced trench process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

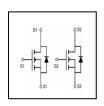
FEATURES

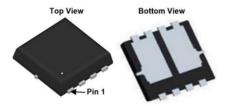
- RDSON \leq 13m Ω @Vgs=10V, Id=15A
- Excellent RDS(ON) and Low Gate Charge

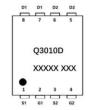
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• Lead free product is acquired

SYMBOL







PDFN3.3X3.3-8L(Dual)

Marking and pin Assignment

ASSEMBLY MESSAGE

Product Name	Marking	Package	Packaging
BXT130N03E	Q3010D	PDFN3.3X3.3-8L	Reel

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Parameter		Symbol	Rating	Unit	
			PDFN3.3X3.3-8L		
Drain-Source Voltage	Drain-Source Voltage			30	V
C C		tinuous (T _C = 25°C)	I-	22	Α
Drain Current	Con	tinuous (T _C = 100°C)	l _D	14	Α
Drain Current Pulsed (Note1)		I _{DM}	88	Α	
Gate-Source Voltage		V_{GSS}	±20	V	
Power Dissipation T _C =25°C		PD	9.8	W	
Maximum Junction Temperature		TJ	150	°C	
Storage Temperature Range		T _{STG}	-55 to 150	°C	

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

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THERMAL CHARACTERISTICS

Parameter	Symbol	Max.	Unit	
Farameter	Symbol	PDFN3.3X3.3-8L	Unit	
Thermal Resistance, Junction to Case	Rejc	12.8	°C/W	

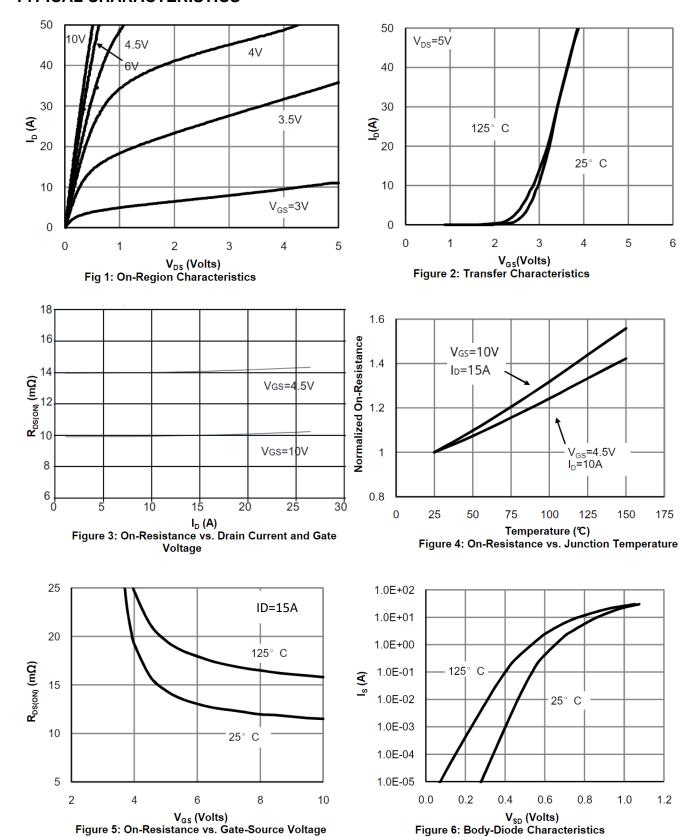
ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
OFF CHARACTERISTICS				•		
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V, ID=250µA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	VDS=30V, VGS=0V			1	uA
Gate-Body Leakage Current, Forward	-	VGS=20V			100	nA
Gate-Body Leakage Current, Reverse	I _{GSS}	VGS=-20V			-100	nA
ON CHARACTERISTICS			•	•		
Gate Threshold Voltage	V _{GS(TH)}	VDS=VGS, ID=250µA	1.0	1.5	2.5	V
Drain Source On State Desistance	D	VGS=10V, ID=15A		10	13	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	VGS=4.5V, ID=10A		14	19	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	Ciss	V/D0_45\/_\/00_0\/		545		pF
Output Capacitance	Coss	VDS=15V, VGS=0V, f=1.0MHz		235		pF
Reverse Transfer Capacitance	C _{RSS}			33		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	t _{D(ON)}			6		ns
Turn-ON Rise Time	t _R	VDD=15V, ID=20A, VGS =		5		ns
Turn-OFF Delay Time	t _{D(OFF)}	10V, RG=3Ω		25		ns
Turn-OFF Fall-Time	t _F			7		ns
Total Gate Charge(Note2)	Q_{G}	VDC 45V VCC 40V ID		19		nC
Gate Source Charge	Q _{GS}	VDS =15V, VGS =10V, ID =10A		6.3		nC
Gate Drain Charge	Q _{GD}	=10A		4.5		nC
SOURCE- DRAIN DIODE RATINGS	AND CHARA	ACTERISTICS	•			
Drain-Source Diode Forward Voltage	V _{SD}	IS=22A, VGS=0V			1.2	V
Diode Continuous Forward Current	ls				22	Α
Maximum Pulsed Drain to Source	Ism				88	Α
Diode Forward Current	IJIVI				00	/\
Body Diode Reverse Recovery Time	trr	 IF=10A,dI/dt=100A/μs		7		ns
Body Diode Reverse Recovery Charge	Qrr	π -10A, αι/ αι-100A/ μS		6.3		nC

Note: 2. Essentially independent of operating temperature



TYPICAL CHARACTERISTICS





TYPICAL CHARACTERISTICS(Cont.)

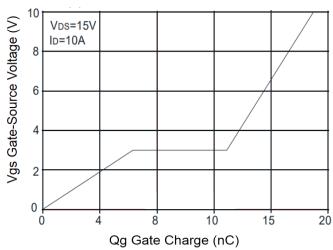


Figure 7: Gate-Charge Characteristics

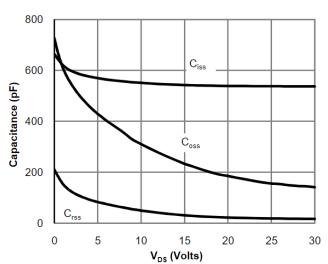


Figure 8: Capacitance Characteristics

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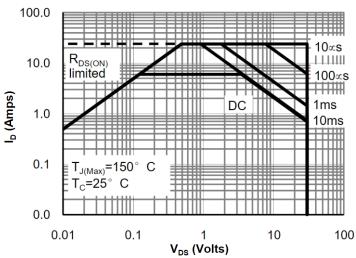
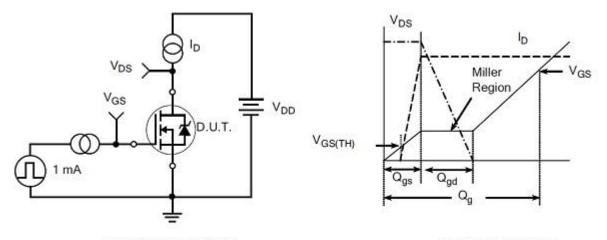


Figure 9: Maximum Forward Biased Safe Operating Area

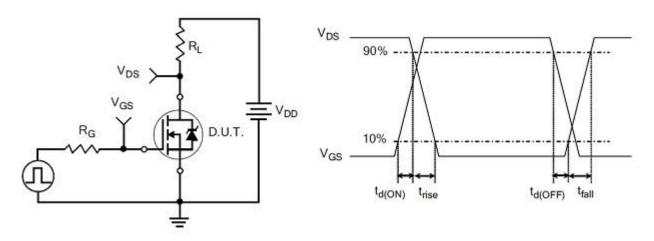


TEST CIRCUITS AND WAVEFORMS





Gate Charge Waveform

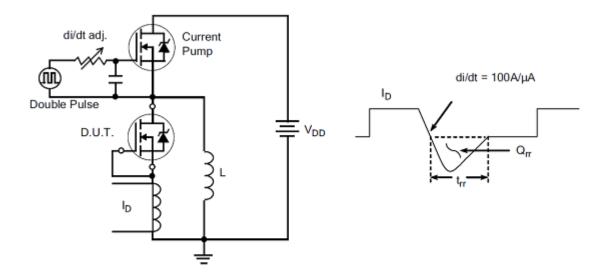


Resistive Switching Test Circuit

Resistive Switching Waveforms

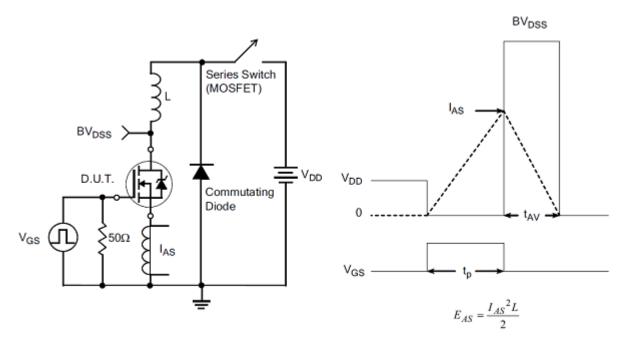


TEST CIRCUITS AND WAVEFORMS(Cont.)



Diode Reverse Recovery Test Circuit

Diode Reverse Recovery Waveform



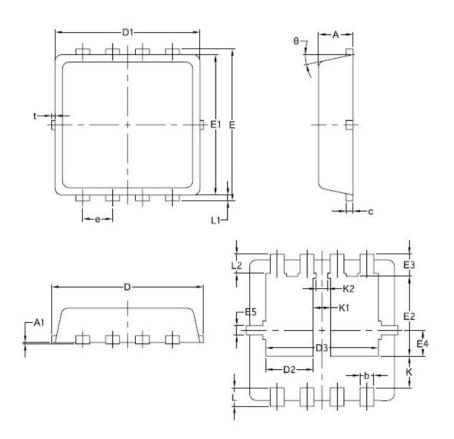
Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

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PDFN3.3X3.3-8L Package



50	S	COMMON			
	M B O	MM			
	ů.	MIN	NOM	MAX	
	Α	The second conservation of the second second		0.85	
	A1	/	/	0.05	
	b	0.25	0.30	0.39	
	С	0.14	0.152	0.20	
	D	3.20	3.30	3.45	
	D1	3.05	3.15	3.25	
	D2	0.84	1.04	1.24	
	D3	2.30	2.45	2.60	
	Е	3.20	3.30	3.40	
	E1	2.95	3.05	3.15	
	E2	1.60	1.74	1.90	
/2	E3	0.28	0.48	0.65	
	E4	0.37	0.57	0.77	
	E5	0.10	0.20	0.30	
	е	0.60	0.65	0.70	
	K	0.50	0.69	0.80	
	K1	0.30	0.38	0.53	
	K2	0.15	0.25	0.35	
	L	0.30	0.40	0.50	
	L1	0.06	0.125	0.20	
	L2	0.27	0.42	0.57	
	t	0	0.075	0.13	
	θ	10°	12°	14°	

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Revision history

Document revision history

Date	Revision	Changes
20-Mar-2021	1.0	First release

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